



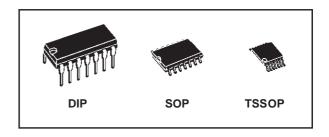
# **HEX INVERTER**

- HIGH SPEED: t<sub>PD</sub> = 8ns (TYP.) at V<sub>CC</sub> = 6V
- LOW POWER DISSIPATION:  $I_{CC} = 1\mu A(MAX.)$  at  $T_A=25^{\circ}C$
- HIGH NOISE IMMUNITY: V<sub>NIH</sub> = V<sub>NIL</sub> = 28 % V<sub>CC</sub> (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I<sub>OH</sub>| = I<sub>OL</sub> = 4mA (MIN) at V<sub>CC</sub> = 4.5V
- BALANCED PROPAGATION DELAYS: tplh ≅ tphl
- WIDE OPERATING VOLTAGE RANGE: V<sub>CC</sub> (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 04



The M74HC04 is an high speed CMOS HEX INVERTER fabricated with silicon gate C<sup>2</sup>MOS technology.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

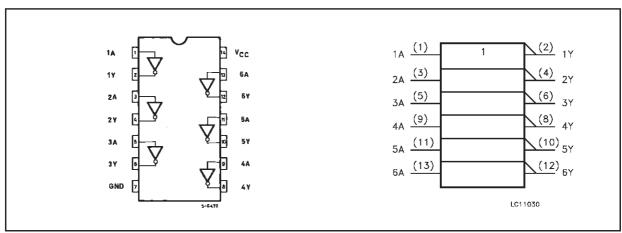


#### **ORDER CODES**

PACKAGE	TUBE	T & R
DIP	M74HC04B1R	
SOP	M74HC04M1R	M74HC04RM13TR
TSSOP		M74HC04TTR

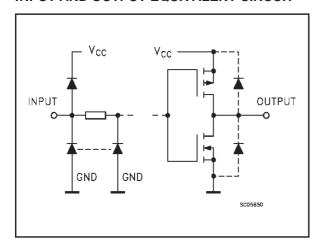
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



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### INPUT AND OUTPUT EQUIVALENT CIRCUIT



### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9, 11, 13	1A to 6A	Data Inputs
2, 4, 6, 8, 10, 12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

### **TRUTH TABLE**

Α	Υ
L	Н
Н	L

### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
P <sub>D</sub>	Power Dissipation	500(*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied (\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	Supply Voltage		2 to 6	V
V <sub>I</sub>	Input Voltage		0 to V <sub>CC</sub>	V
Vo	Output Voltage		0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	V <sub>CC</sub> = 2.0V	0 to 1000	ns
t <sub>r</sub> , t <sub>f</sub>		V <sub>CC</sub> = 4.5V	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

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### **DC SPECIFICATIONS**

		Test Condition					Value				
Symbol	Parameter	er V <sub>CC</sub>		T <sub>A</sub> = 25°C -40 to				85°C -55 to 125°C			Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
V <sub>IL</sub>	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V <sub>OH</sub>	High Level Output	2.0	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9		
	Voltage	4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I <sub>O</sub> =-20 μA	5.9	6.0		5.9		5.9		V
		4.5	I <sub>O</sub> =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I <sub>O</sub> =-5.2 mA	5.68	5.8		5.63		5.60		
V <sub>OL</sub>	Low Level Output	2.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		6.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I <sub>O</sub> =5.2 mA		0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
I <sub>CC</sub>	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			1		10		20	μΑ

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ns}$ )

		Test Condition		Value							
Symbol	Parameter	Vcc		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		Unit
		V <sub>CC</sub> (V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t <sub>tLH</sub> t <sub>tHL</sub>	Output Transition	2.0			38	75		95		110	
	Time	4.5			8	15		19		22	ns
		6.0			6	13		16		19	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay	2.0			45	95		120		145	
	Time	4.5			9	19		24		29	ns
		6.0			8	16		20		25	

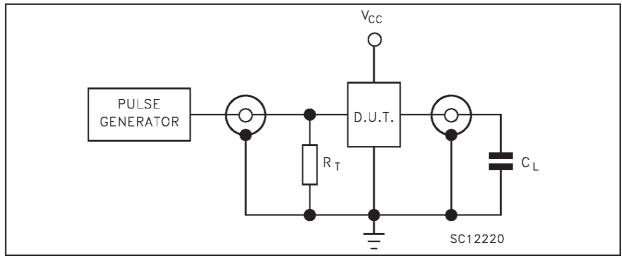
### **CAPACITIVE CHARACTERISTICS**

		7	Test Condition	Value							
Symbol	Parameter	V <sub>CC</sub> (V)		Ţ	<sub>A</sub> = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance	5.0			5	10		10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	5.0			22						pF

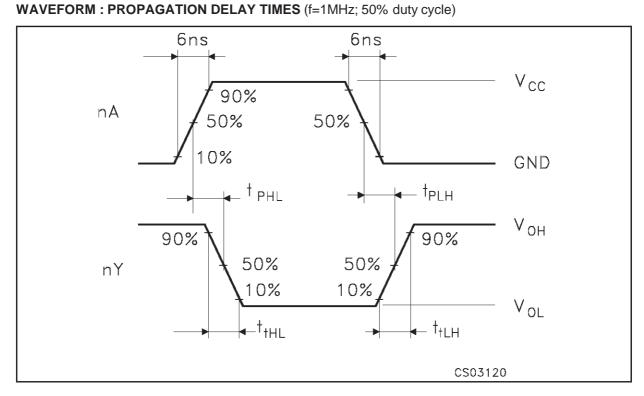
<sup>1)</sup>  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6$  (per Gate)

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### **TEST CIRCUIT**



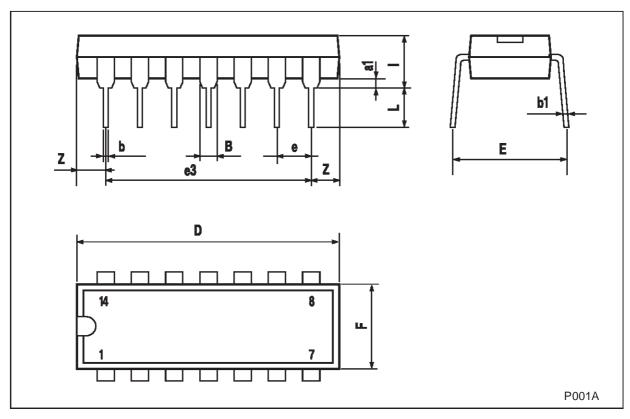
 $C_L$  = 50pF or equivalent (includes jig and probe capacitance)  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )



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# Plastic DIP-14 MECHANICAL DATA

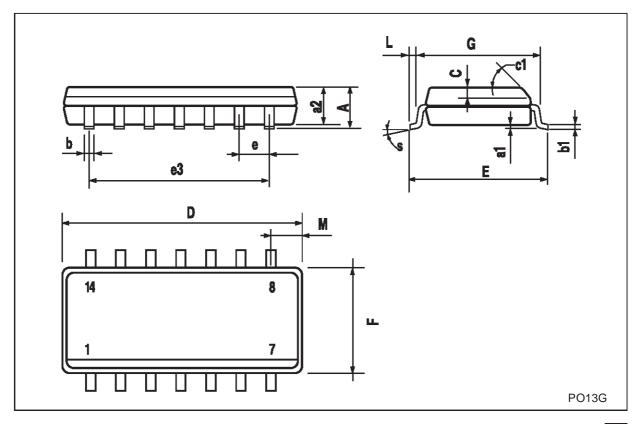
DIM.		mm.			inch	
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



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# **SO-14 MECHANICAL DATA**

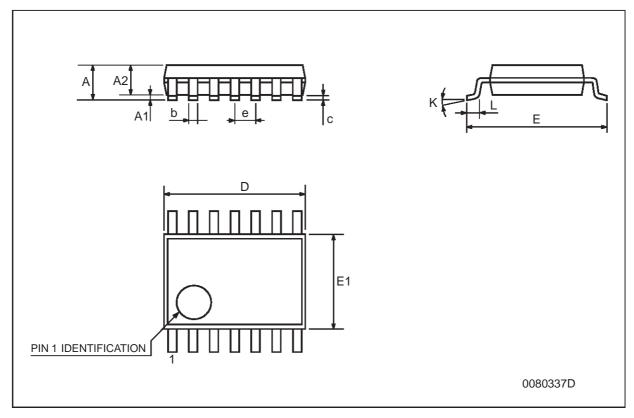
DIM.		mm.			inch	
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)		
D	8.55		8.75	0.336		0.344
Е	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.68			0.026
S			8° (ı	max.)		



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# **TSSOP14 MECHANICAL DATA**

DIM.		mm.			inch	inch		
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
E	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		



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